

Resource Summary Report

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Texas State University Oxford ICP/RIE system

RRID:SCR_028203

Type: Tool

Proper Citation

Texas State University Oxford ICP/RIE system (RRID:SCR_028203)

Resource Information

URL: <https://sro.txst.edu/sro-facilities/sro-nrsc.html>

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Description: Facility Oxford ICP-RIE Plaslab 180 utilizes a 3kW RF power supply to generate a remote plasma of Cl₂, BCl₃, H₂, Ar, NF₃, O₂, SF₆, and/or C₄F₈ gas species that can be further accelerated (300W table bias) toward a substrate resulting in a combination of physical and chemical dry etching for material removal. The turbomolecular pumped system achieves a base pressure 1E-7 Torr and is equipped with chuck temperature control from -110 to 350 degrees C. Advanced dry etching system combining inductively coupled plasma (ICP) and reactive ion etching (RIE) for highly anisotropic, high-precision material removal in semiconductor and nanofabrication processes.

Synonyms: Oxford ICP/RIE (PlasmaPro 100)

Resource Type: instrument resource

Keywords: ICP, RIE, dry etching, plasma etching, semiconductor fabrication, nanofabrication

Availability: Restricted

Resource Name: Texas State University Oxford ICP/RIE system

Resource ID: SCR_028203

Record Creation Time: 20260327T054534+0000

Record Last Update: 20260912T200545+0000

Ratings and Alerts

No rating or validation information has been found for Texas State University Oxford ICP/RIE system.

No alerts have been found for Texas State University Oxford ICP/RIE system.

Data and Source Information

Source: [SciCrunch Registry](#)

Usage and Citation Metrics

We have not found any literature mentions for this resource.